

SD103AWX;SD103BWX;SD103CWX

Schottky Diode

FEATURE

- Low Power Loss For High Efficiency
- Low Forward Voltage Schottky Rectifier
- SOD323 Micro SMD package
- RoHS compliant / Green EMC
- Matte Tin (Sn) Lead finish
- Cathode Band / Device marking

MARKING:

SD103AWX	S4
SD103BWX	S5
SD103CWX	S6

SOD-323-GW



Schematic diagram



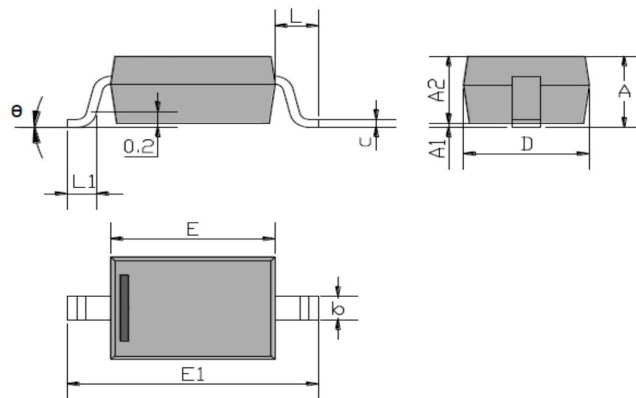
ABSOLUTE MAXIMUM RATINGS ($T_a=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Value			Unit
		SD103 AWX	SD103 BWX	SD103 CWX	
Non-Repetitive Peak Reverse Voltage	V_{RM}	40	30	20	V
Repetitive Peak Reverse Voltage	V_{RRM}	40	30	20	V
RMS Reverse Voltage	$V_{R(RMS)}$	28	21	14	V
Average Rectified Output Current	I_O	350			mA
Non-Repetitive Peak Forward Surge Current (@ $t=8.3\text{ms}$)	I_{FSM}	2			A
Power Dissipation	P_D	200			mW
Junction Temperature	T_J	125			$^\circ\text{C}$
Storage Temperature	T_{STG}	-55 to +125			$^\circ\text{C}$

ELECTRICAL CHARACTERISTICS(T_a=25°C unless otherwise noted)

Parameter	Symbol	Test Condition		Min	Type	Max	Unit
Reverse brekedown Voltage	V _{BR}	I _R =100uA	SD103AWX	40			V
		I _R =100uA	SD103BWX	30			
		I _R =100uA	SD103CWX	20			
Forward Voltage	V _F	I _F =20mA				0.37	V
		I _F =200mA				0.6	
Reverse current	I _R	V _R =30V	SD103AWX			5.0	uA
		V _R =20V	SD103BWX			5.0	
		V _R =10V	SD103CWX			5.0	
Total capacitance	C _{tot}	V _R =0V,f=1MHz				50	pF
Reverse recovery time	trr	I _F = I _R =200mA, Irr=0.1*I _R , R _L =100Ω			10		ns

SOD-323-GW Package Information



Symbol	Dimensions In Millimeters		
	Min	Typ	Max
A	-	-	1.000
A1	0.000	-	0.100
A2	0.800	-	0.900
b	0.250	-	0.350
c	0.080	-	0.150
D	1.200	-	1.400
E	1.600	-	1.800
E1	2.500	-	2.700
L	0.475 REF.		
L1	0.250	-	0.400
θ	0°	-	8°

1.Unit mm